

Christoffer Kauppinen

List of Publications by Year in descending order

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papers

291
citations

1039406

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all docs

19
docs citations

19
times ranked

449
citing authors

#	ARTICLE	IF	CITATIONS
1	Superhydrophobic Antireflection Coating on Glass Using Grass-like Alumina and Fluoropolymer. ACS Applied Materials & Interfaces, 2020, 12, 49957-49962.	4.0	51
2	Grass-like Alumina with Low Refractive Index for Scalable, Broadband, Omnidirectional Antireflection Coatings on Glass Using Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2017, 9, 15038-15043.	4.0	38
3	Atomic layer etching of gallium nitride (0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	0.9	37
4	Chemical compatibility of fused filament fabrication-based 3-D printed components with solutions commonly used in semiconductor wet processing. Additive Manufacturing, 2018, 23, 99-107.	1.7	33
5	Atomic Layer Engineering of Er-Ion Distribution in Highly Doped Er:Al ₂ O ₃ for Photoluminescence Enhancement. ACS Photonics, 2016, 3, 2040-2048.	3.2	27
6	Selective terahertz emission due to electrically excited 2D plasmons in AlGaIn/GaN heterostructure. Journal of Applied Physics, 2019, 126, .	1.1	26
7	MOVPE growth of N-polar AlN on 4H-SiC: Effect of substrate miscut on layer quality. Journal of Crystal Growth, 2018, 487, 12-16.	0.7	20
8	Epi-Gd ₂ O ₃ /AlGaIn/GaN MOS HEMT on 150-µm Si wafer: A fully epitaxial system for high power application. Applied Physics Letters, 2019, 115, 063502.	1.5	14
9	Fluorescence-enhancing plasmonic silver nanostructures using azopolymer lithography. RSC Advances, 2016, 6, 48129-48136.	1.7	9
10	A technique for large-area position-controlled growth of GaAs nanowire arrays. Nanotechnology, 2016, 27, 135601.	1.3	9
11	MOVPE growth of GaN on 6-inch SOI-substrates: effect of substrate parameters on layer quality and strain. Semiconductor Science and Technology, 2017, 32, 045003.	1.0	9
12	High-Definition Nanoimprint Stamp Fabrication by Atomic Layer Etching. ACS Applied Nano Materials, 2018, 1, 2476-2482.	2.4	7
13	Grass-like alumina coated window harnesses the full omnidirectional potential of black silicon photodiodes. Applied Optics, 2021, 60, 10415.	0.9	3
14	Two-dimensional plasmons in a GaN/AlGaIn heterojunction. Journal of Physics: Conference Series, 2019, 1199, 012014.	0.3	2
15	Site-specific growth of oriented ZnO nanocrystal arrays. Beilstein Journal of Nanotechnology, 2019, 10, 274-280.	1.5	2
16	Metalorganic vapor phase epitaxy of wurtzite InP nanowires on GaN. Applied Physics Letters, 2020, 116, 093101.	1.5	2
17	Back-Contacted Carrier Injection for Scalable GaN Light Emitters. Physica Status Solidi (A) Applications and Materials Science, 2022, 219, 2100461.	0.8	2
18	Terahertz Emission due to Radiative Decay of Hot 2D Plasmons in AlGaIn/GaN Heterojunction. , 2019, , .		0

#	ARTICLE	IF	CITATIONS
19	2D electrons and 2D plasmons in AlGaIn/GaN nanostructure under highly non-equilibrium conditions. Journal of Physics: Conference Series, 2020, 1482, 012022.	0.3	0